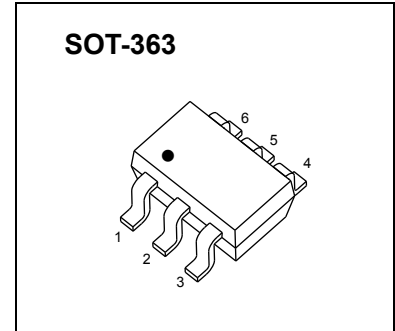


Plastic-Encapsulate MOSFETS

N-channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60 V	5Ω@10V	300mA
	5.3Ω@4.5V	



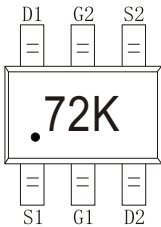
FEATURE

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected

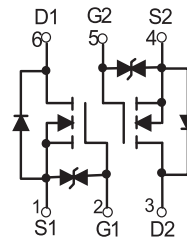
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



MOSFET MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	±20	V
I_D	Drain Current	300	mA
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C/W

MOSFET ELECTRICAL CHARACTERISTICS

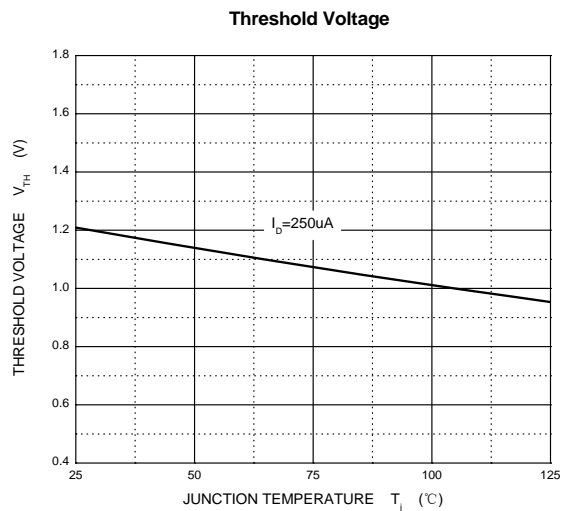
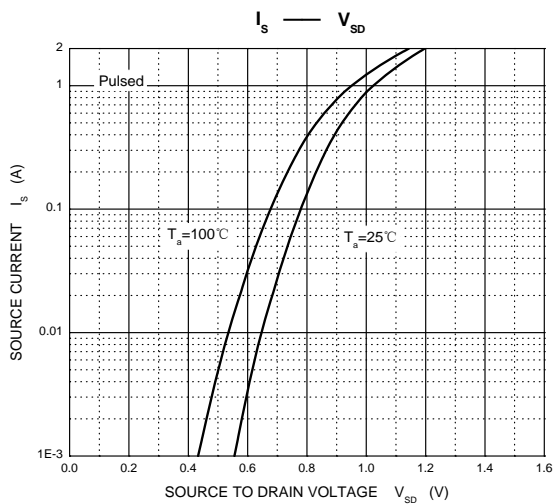
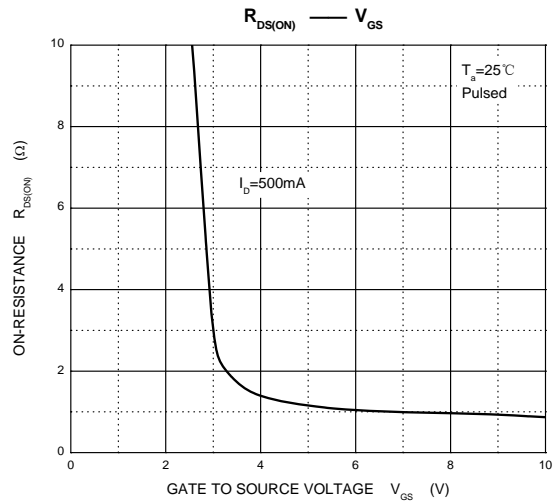
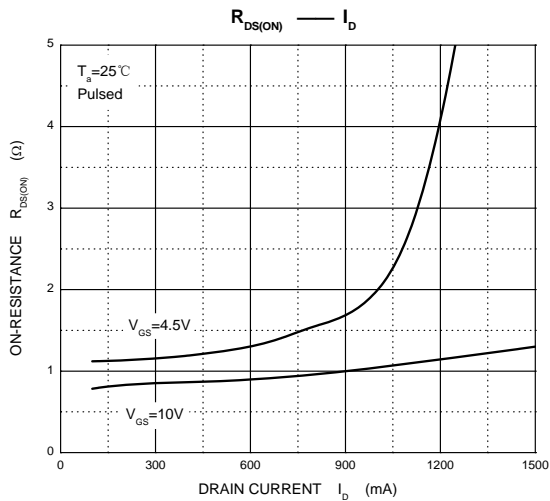
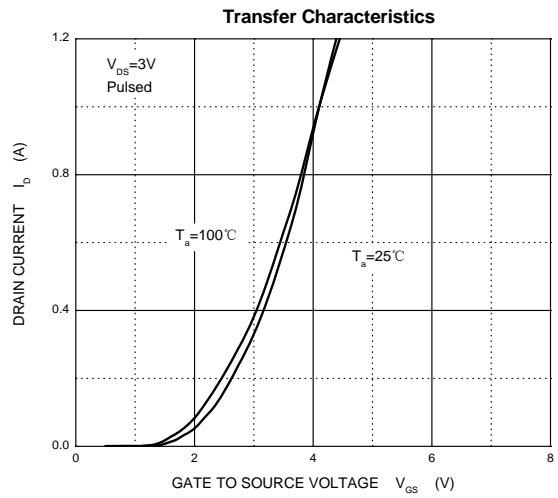
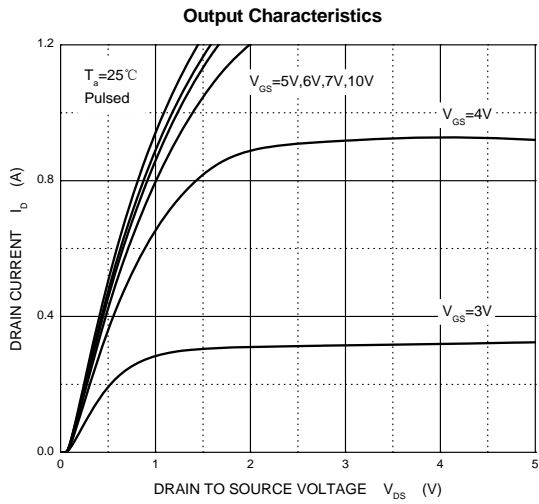
$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate –Source leakage current	I_{GSS1}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 200mA$		1.1	5.3	Ω
		$V_{GS} = 10V, I_D = 500mA$		0.9	5	Ω
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 300mA$			1.5	V
Recovered charge	Q_r	$V_{GS} = 0V, I_S = 300mA, V_R = 25V,$ $di_S/dt = -100A/\mu s$		30		nC
Dynamic Characteristics**						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
Switching Characteristics**						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega,$ $R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 300mA, V_R = 25V,$ $di_S/dt = -100A/\mu s$		30		ns
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	$I_{GS} = \pm 1mA$ (Open Drain)	± 21.5		± 30	V

Notes :

*Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

**These parameters have no way to verify.



SOT-363-Package Outline Dimensions

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